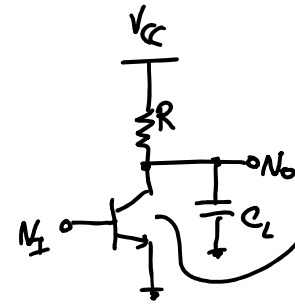


Lecture 37: CMOS Inverter

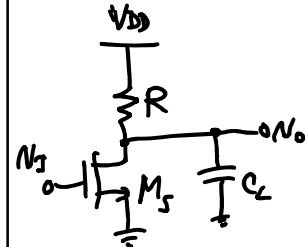
- Announcements:
- First 15 minutes of lecture for HKN course evaluations
- HW#11 is online and due Tuesday, Dec. 10
- Lab 6 online and due 5 p.m., Friday, Dec. 13
- -----
- Lecture Topics: (over the next few days)
  - ↳ MOS Inverter w/ Resistive Load
  - ↳ Static CMOS Inverter Behavior
    - $V_{OL}$  and  $V_{OH}$
    - $V_{IL}$  and  $V_{IH}$
  - ↳ Dynamic CMOS Inverter Behavior
    - Propagation Delay
    - Capacitance
  - ↳ Astable Ring Oscillator
  - ↳ CMOS Inverter Propagation Delay
- -----
- Last Time:
- Started digital circuits
- Now, continue with this...

Transistor Inverter w/ Resistive Load

⇒ use Xriston as a switching device → allows it to handle large signals



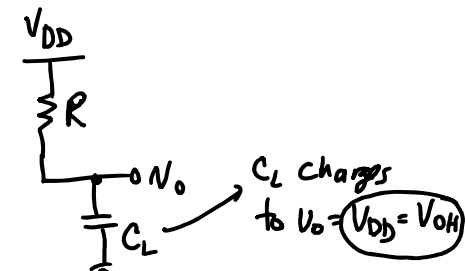
bipolar Xriston (first inverters used bipolar technology)  
 But... not as good as MOS for digital electr.  
 ↳ reasons: cost & power consumption



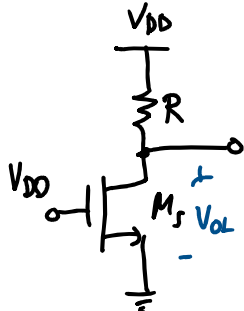
} Find  $V_{OH}$  &  $V_{OL}$ .  
 (for this resistively-loaded MOS Inverter)

$V_{OH}: N_I \leq V_{IL} \rightarrow \text{say } N_{IC} = 0V$

⇒  $M_S$  off



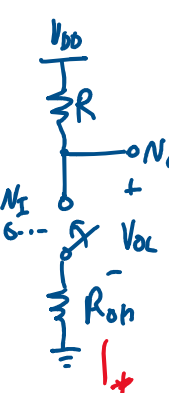
$V_{OL}: N_I = V_{IH} \rightarrow$  say  $N_I = V_{DD}$   
 $\Rightarrow M_S$  on  
 $\Rightarrow$  in steady-state:



For  $M_S: V_{GS} - V_{THS} = V_{DD} - V_{THS} > V_{OL}$   
 $\therefore M_S$  is linear  
 $V_{OL} = V_{DD} - I_D R$   
 $I_D = \mu_n C_{ox} \left(\frac{W}{L}\right)_S (V_{DD} - V_{THS} - \frac{V_{OL}}{2}) V_{OL}$

$$V_{OL} = V_{DD} - \mu_n C_{ox} \left(\frac{W}{L}\right)_S (V_{DD} - V_{THS}) V_{OL} + \frac{\mu_n C_{ox} \left(\frac{W}{L}\right)_S V_{OL}^2}{2}$$

$\Rightarrow$  solve quadratic for  $V_{OL}$   
 $\Rightarrow$  or can get a less accurate (but still good) value ...  
 $\Rightarrow$  ... by defining an ON-resistance for the switching device:

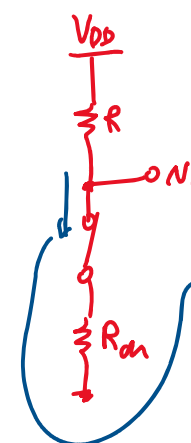


$$V_{OL} = V_{DD} \frac{R_{on}}{R + R_{on}} = V_{DD} \left( \frac{1}{1 + \frac{R}{R_{on}}} \right)$$

$$R_{on} = \frac{V_{DS}}{i_D} = \frac{V_{OL}}{\mu_n C_{ox} \left(\frac{W}{L}\right)_S (V_{DD} - V_{THS} - \frac{V_{OL}}{2}) V_{OL}}$$

$$R_{on} = \frac{1}{\mu_n C_{ox} \left(\frac{W}{L}\right)_S (V_{DD} - V_{THS} - \frac{V_{OL}}{2})}$$

When  $N_O = V_{OL}$ :



$I = \frac{V_{DD}}{R + R_{on}} =$  In digital, any current is too much!  
 say  $I = 1 \mu A \rightarrow$  okay for 100x shorter = 100  $\mu A$   
 But for 1 billion  $\rightarrow 1000 A \rightarrow$  way too much

Thus, need lower power consumption!  
 $\Downarrow$   
 CMOS!

**The CMOS Inverter**

⇒ introduce a complimentary device to ideally eliminate static power!

Get  $V_{OH}$  &  $V_{OL}$ :

① Case:  $V_I < V_{IL}$   
 $M_p$  on,  $M_n$  off

$\therefore V_{OH} = V_{DD}$   
in steady-state

② Case:  $V_I > V_{IH}$   
 $M_p$  off,  $M_n$  on

$\therefore V_{OL} = 0V$   
in steady-state

**Determination of the Voltage Transfer Characteristic (VTC)**